NSN 5961-01-312-4663

Unitized Semiconductor Devices - Page 1 of 1

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Inclosure Material:

Ceramic

Overall Length:

92.0 millimeters

Overall Height:

20.0 millimeters

Overall Width:

30.0 millimeters

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-240aa

Component Name And Quantity:

2 semiconductor device thyristor

Mounting Method:

Press fit

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon all semiconductor device thyristor

Voltage Rating In Volts Per Characteristic:

1300.0 nonrepetitive peak reverse voltage all semiconductor device thyristor and 1200.0 repetitive peak off-state voltage all semiconductor device thyristor and 1200.0 repetitive peak reverse voltage all semiconductor device thyristor

Current Rating Per Characteristic:

60.00 amperes forward current, total rms universal all semiconductor device thyristor

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius junction

Special Features:

All semiconductor deivce thyristor junction pattern arrangement: pnpn

Terminal Type And Quantity:

5 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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